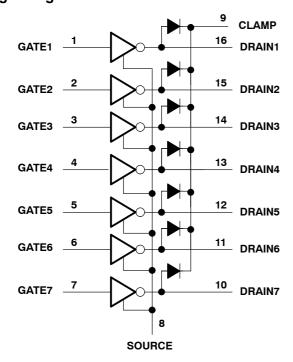
- Seven 0.5-A Independent Output Channels
- Integrated Clamp Diode With Each Output
- Low r_{DS(on)} . . . 0.5 Ω Typical
- Output Voltage . . . 60 V
- Pulsed Current . . . 3 A Per Channel
- Avalanche Energy . . . 22 mJ

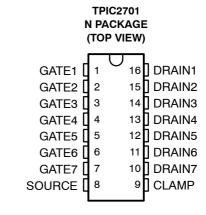
description

The TPIC2701 is a monolithic power DMOS transistor array that consists of seven independent N-channel enhancement-mode DMOS transistors connected in a common-source configuration with open drains. The TPIC2701 is pin-for-pin functionally compatible with the Texas Instruments ULN2001A through ULN2004A.

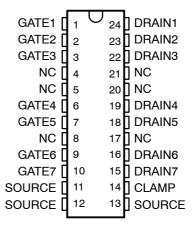
The TPIC2701 is characterized for operation over a temperature range of 0°C to 125°C.The TPIC2701M is characterized for operation over the full military temperature range of -55°C to 125°C.

logic diagram





TPIC2701M J PACKAGE[†] (TOP VIEW)



NC - No internal connection

† Refer to the mechanical data for the JW package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



absolute maximum ratings over operating case temperature range (unless otherwise noted)

Drain-source voltage, V _{DS}	60 V
Gate-source voltage, V _{GS}	±20 V
Clamp-drain voltage, V _{CD}	
Continuous source-drain diode current	
Pulsed drain current, each output, I _D (see Note 1 and Figure 17)	
Pulsed clamp current, I _{CL} (see Note 1 and Figure 18)	
Continuous drain current, each output, all outputs on	
Single-pulse avalanche energy, E _{AS} (see Figure 4)	
Continuous total power dissipation	
Operating virtual junction temperature range, T _{.J} : TPIC2701	
	–55°C to 150°C
Operating case temperature range, T _{C:} TPIC2701	
TPIC2701M	
Storage temperature range, T _{stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: N Package.	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: J Package .	
E 1: Pulse duration = 10 ms. duty cycle = 6%.	

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
J	2660 mW	21.3 mW/°C	1701 mW	1382 mW	530 mW
N	1400 mW	11.0 mW/°C	905 mW	740 mW	300 mW

electrical characteristics, T_C = 25°C (unless otherwise noted)

	DADAMETED	TEOT 001151710	NO.	TI	PIC2701		
	PARAMETER	TEST CONDITIO	INS	MIN	TYP	MAX	UNIT
V _{(BR)DS}	Drain-source breakdown voltage	$I_D = 1 \mu A$, $V_{GS} = 0$		60			V
V_{TGS}	Gate-source threshold voltage	$I_D = 1 \text{ mA}, \qquad V_{DS} = V_{GS}$		1.2	1.75	2.4	V
V _{DS(on)}	Drain-source on-state voltage	I_D = 0.5 A, V_{GS} = 15 V, See Notes 2 and 3		0.25	0.4	V	
	7	V 40 V V 0	T _C = 25°C		0.05	1	
I _{DSS}	Zero-gate-voltage drain current	$V_{DS} = 48 \text{ V}, V_{GS} = 0$	T _C = 125°C		0.5	10	μΑ
I _{GSSF}	Forward gate current, drain short circuited to source	V _{GS} = 20 V, V _{DS} = 0			10	100	nA
I _{GSSR}	Reverse gate current, drain short circuited to source	$V_{GS} = -20 \text{ V}, V_{DS} = 0$			10	100	nA
		$V_{GS} = 15 \text{ V}, I_D = 0.5 \text{ A},$	T _C = 25°C		0.5	0.8	
r _{DS(on)}	Forward drain-source on-state resistance	See Notes 2 and 3 and Figures 5 and 6	T _C = 125°C		0.8	1.3	Ω
g _{fs}	Forward transconductance	V_{DS} = 15 V, I_D = 0.5 A, See Notes 2 and 3		0.5	0.8		S
C _{iss}	Short-circuit input capacitance, common source				105		
C _{oss}	Short-circuit output capacitance, common source	V _{DS} = 25 V, V _{GS} = 0,	f – 300 kHz		65		1 ne
C _{rss}	Short-circuit reverse transfer capacitance, common source	VDS - 23 V, VGS = 0,	1 – 300 KI IZ		15		pF

NOTES: 2. Technique should limit $T_J - T_C$ to 10°C maximum.

3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts with a single output transistor conducting.



electrical characteristics over case temperature operating range (unless otherwise noted) (see Note 4)

	DADAMETED	TEOT 00	UDITIONO	- +	TP	IC2701	М	
	PARAMETER	TEST CO	NDITIONS	T _C [†]	MIN	TYP	MAX	UNIT
V	Dunin to accuracy handlade way will be a	$I_D = 1 \mu A$,	V _{GS} = 0	25°C	00			V
V _{(BR)DS}	Drain-to-source breakdown voltage	$I_D = 1 \text{ mA},$	V _{GS} = 0	Full range	60			V
V_{TGS}	Gate-to-source input threshold voltage	$I_D = 1 \text{ mA},$	$V_{DS} = V_{GS}$	Full range	1.2	1.75	2.4	V
,	Due:- to course on state walks as		V 45V	25°C		0.25	0.45	V
V _{DS(on)}	Drain-to-source on-state voltage	$I_D = 0.5 A,$	$V_{GS} = 15 V$	Full range			0.65	V
		,, ,,,,,	., .	25°C		0.05	1	
IDSS	Zero-gate-voltage drain current	$V_{DS} = 48 V$,	$V_{GS} = 0$	Full range			10	μΑ
	Forward gate current, drain short-circuited to	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	., .	25°C		10	100	nA
IGSSF	source	$V_{GS} = 20 \text{ V},$	$V_{DS} = 0$	Full range			10	μΑ
	Reverse gate current, drain short-circuited to		., .	25°C		10	100	nA
IGSSR	source	$V_{GS} = -20 \text{ V},$	$V_{DS} = 0$	Full range			10	μΑ
				25°C		0.5	0.9	0
r _{DS(on)}	Forward drain-source on-state resistance	$V_{GS} = 15 V$,	$I_D = 0.5 A$	Full range			1.3	Ω
g _{fs}	Forward transconductance	$V_{DS} = 15 V$,	I _D = 0.5 A	25°C		0.8		S
C _{iss}	Short-circuit input capacitance, common source					105		
C _{oss}	Short-circuit output capacitance, common source	V _{DS} = 25 V, V _{GS} = 0,		Full range		65		~F
C _{rss}	Short-circuit reverse transfer capacitance, common source	f = 300 kHz		Full range		15		- pF

[†] Full range is – 55°C to 125°C.

NOTE 4: Pulse testing techniques are used to maintain the virtual junction temperature as close to the case temperature as possible. Thermal effects must be taken into account separately.

source-drain diode characteristics, $T_C = 25^{\circ}C$

PARAMETER		TEST SOMETIONS	Т	TPIC2701			
		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
V_{SD}	Forward On voltage	$I_S = 0.5 \text{ A}, V_{GS} = 0$		0.9	1.4	V	
t _{rr(SD)}	Reverse-recovery time	$I_S = 0.5 \text{ A}, V_{GS} = 0, V_{DS} = 48 \text{ V},$		165		ns	
Q_{RR}	Total source-drain diode charge	di/dt = 25 A/μs, See Figure 1		250		nC	

source-to-drain diode characteristics over operating case temperature range (unless otherwise noted) (see Note 4)

DADAMETED		TEO	TEST CONDITIONS			TPIC2701M			
	PARAMETER	IES	MIN	TYP	MAX	UNIT			
V_{SD}	Forward On voltage	I _S = 0.5 A,	V _{GS} = 0			0.9	1.4	V	
t _{rr}	Reverse recovery time	I _S = 0.5 A,	V _{GS} = 0,	V _{DS} = 48 V,		165		ns	
Q_{RR}	Total source-to-drain diode charge	di/dt = 25 A/μs,	$T_C = 25^{\circ}C$,	See Figure 1		250		nC	

NOTE 4: Pulse testing techniques are used to maintain the virtual junction temperature as close to the case temperature as possible. Thermal effects must be taken into account separately.



clamp diode characteristics, T_C = 25°C

	DADAMETED	TEST SOUDITIONS	T		UNIT	
PARAMETER		TEST CONDITIONS	MIN	TYP		MAX
V _F	Forward on-voltage	I _F = 0.5 A		1	1.5	V
V_{BR}	Breakdown voltage	$I_R = 1 \mu A$	60			٧
I_R	Reverse leakage current	V _R = 48 V		0.05	1	μΑ
t _{rr(CD)}	Reverse-recovery time	I _F = 0.1 A, di/dt = 25 A/μs,		90		ns
Q_{RR}	Total source-drain diode charge	V _{CD} = 48 V, See Figure 1		100		nC

clamp diode characteristics over operating case temperature range (unless otherwise noted) (see Note 4)

	DADAMETED		TEAT AGNIDITIONS		TP	М	UNIT		
	PARAMETER		TEST CONDITIONS				MAX	ONIT	
V_{F}	Forward voltage	I _F = 0.5 A				1	1.5	V	
	Deceloder on visite as	$I_R = 1 \mu A$,	T _C = 25°C		00			٧	
$V_{(BR)}$	Breakdown voltage	I _R = 1 mA	60			V			
	Daviere lealings arment	V 40.V	T _C = 25°C			0.05	1		
^I R	Reverse leakage current	V _R = 48 V					10	μΑ	
t _{rr(SD)}	Reverse recovery time, source-to-drain	I _F = 0.1 A,	di/dt = 25 A/μs,	T _C = 25°C		90		ns	
Q_{RR}	Total source-to-drain diode charge	V_{CD} = 48 V,	See Figure 1			100		nC	

NOTE 4: Pulse testing techniques are used to maintain the virtual junction temperature as close to the case temperature as possible. Thermal effects must be taken into account separately.

resistive-load switching characteristics, $T_C = 25^{\circ}C$

	DADAMETED		TEST COMPLETIONS			TPIC2701			
	PARAMETER		TEST CONDITIONS				MAX	UNIT	
t _{d(on)}	Turn-on delay time					10			
t _{d(off)}	Turn-off delay time	V _{DD} = 25 V,	$R_L = 100 \Omega$, See Figure 2	t _{en} = 10 ns,		30			
t _r	Rise time	t _{dis} = 10 ns,				15		ns	
t _f	Fall time	1				5			
Q_g	Total gate charge					2.8	3.6		
Q _{gs}	Gate-source charge	V _{DS} = 48 V, See Figure 3		$V_{GS} = 10 \text{ V},$		1.6	2	nC	
Q_{gd}	Gate-drain charge	occ riguio c				1.2	1.6		

resistive-load switching characteristics over operating case temperature range (unless otherwise noted) (see Note 4)

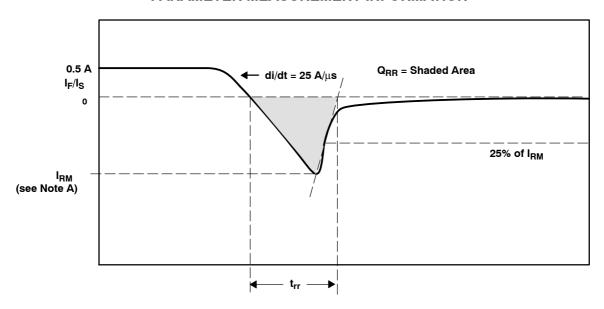
	DADAMETED		TEST CONDITIONS			TPIC2701M			
	PARAMETER	'	MIN	TYP	MAX	UNIT			
t _{d(on)}	Turn-on delay time					10			
t _{d(off)}	Turn-off delay time	V _{DD} = 25 V,	R_L = 100 Ω , See Figure 2	t _{en} = 10 ns,	30			l	
t _r	Rise time	t _{dis} = 10 ns,				15		ns	
t _f	Fall time	1				5			
Q_g	Total gate charge					2.8			
Q_{gs}	Gate-to-source charge	V _{DS} = 48 V, See Figure 3	$I_D = 0.25 A,$	$V_{GS} = 10 \text{ V},$		1.6		nC	
Q _{gd}	Gate-to-drain charge	guio o				1.2			

NOTE 4: Pulse testing techniques are used to maintain the virtual junction temperature as close to the case temperature as possible. Thermal effects must be taken into account separately.

thermal resistance

	PARAMETER	TEST CONDITIONS	TYP	MAX	UNIT	
_	lunction to problem the areal assistance	N package with all outputs at equal power			90	0000
$R_{\theta JA}$ Junction-to-ambient thermal resistance		J package with all outputs at equal power	66			°C/W

PARAMETER MEASUREMENT INFORMATION



NOTE A: I_{RM} = maximum recovery current

Figure 1. Reverse-Recovery-Current Waveforms of Source-Drain and Clamp Diodes

PARAMETER MEASUREMENT INFORMATION

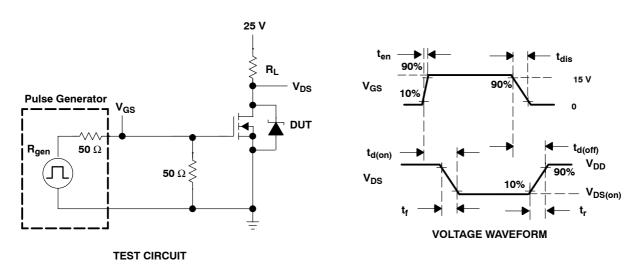


Figure 2. Resistive Switching

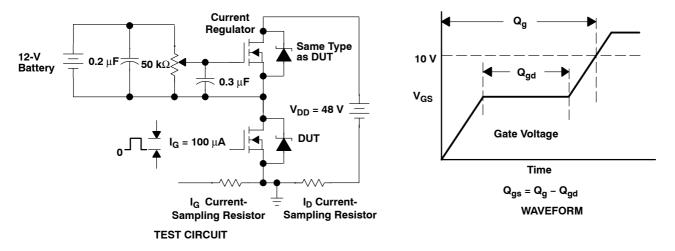
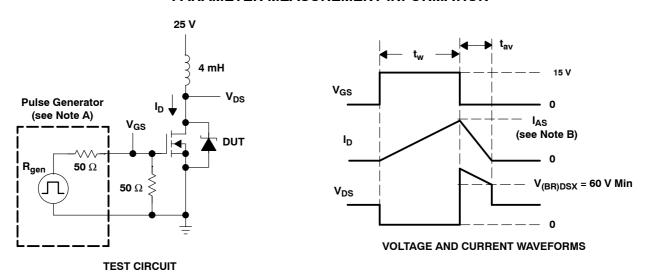


Figure 3. Gate Charge Test Circuit and Waveform

PARAMETER MEASUREMENT INFORMATION



NOTES: A. The pulse generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $Z_O = 50 \ \Omega$.

B. Input pulse duration (t_w) is increased until peak current $I_{AS} = 2.5 A$.

Energy test level is defined as
$$E_{AS} = \frac{I_{AS} \times V_{(BR)DSX} \times t_{av}}{2} = 22 \text{ mJ min.}$$

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

STATIC DRAIN-SOURCE ON-STATE RESISTANCE

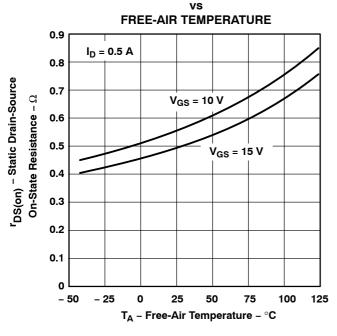


Figure 5

DISTRIBUTION OF FORWARD TRANSCONDUCTANCE TA = 25°C ID = 0.5 A VDS = 15 V O.76 0.775 0.79 0.805 0.82 Grs - Forward Transconductance - S

Figure 7

STATIC DRAIN-SOURCE ON-STATE RESISTANCE

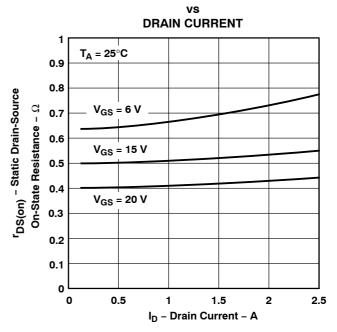


Figure 6

DRAIN-TO-SOURCE CURRENT VS

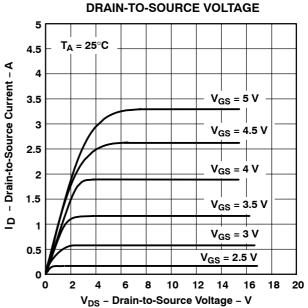


Figure 8



GATE-SOURCE THRESHOLD VOLTAGE

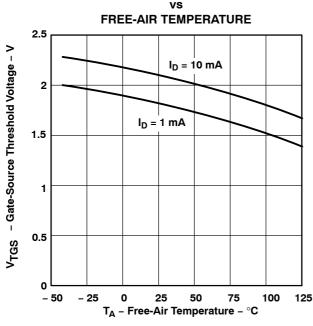


Figure 9

SOURCE-TO-DRAIN DIODE CURRENT vs SOURCE-TO-DRAIN DIODE VOLTAGE

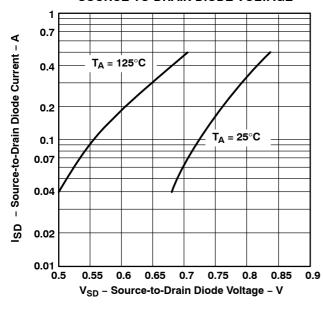


Figure 11

GATE-SOURCE VOLTAGE vs

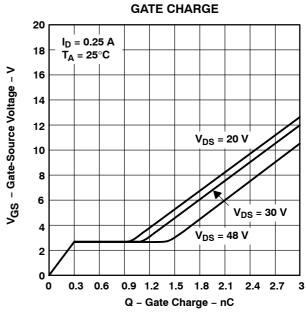


Figure 10

SOURCE-TO-DRAIN DIODE CURRENT vs SOURCE-TO-DRAIN DIODE VOLTAGE

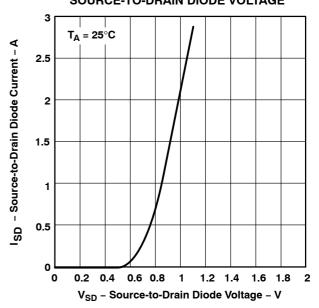
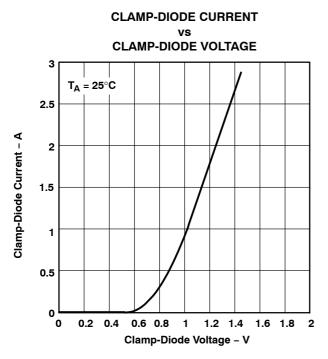


Figure 12



CLAMP-DIODE REVERSE RECOVERY TIME REVERSE di/dt 140 t_{rr} - Clamp-Diode Reverse Recovery Time - ns $I_F = 0.1 A$ 130 V_R = 48 V T_A = 25°C 120 110 100 90 80 70 60 50 40 30 20 30 40 50 60 70 80 100 Reverse di/dt – A/ μ s

Figure 13

Figure 14

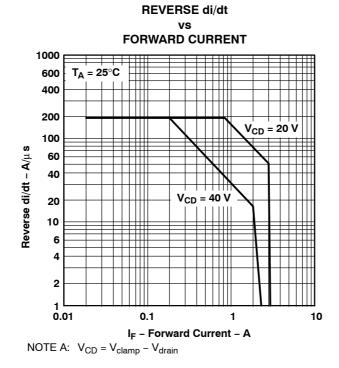


Figure 15



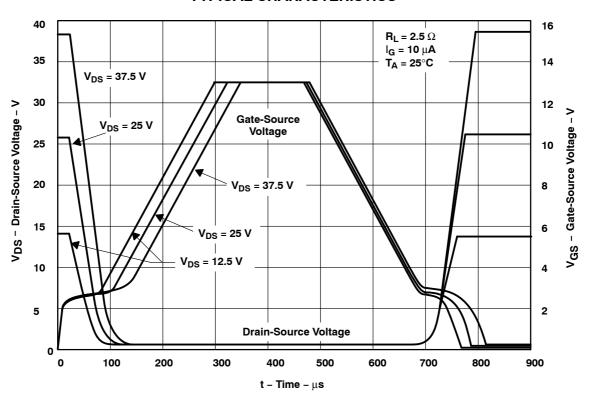
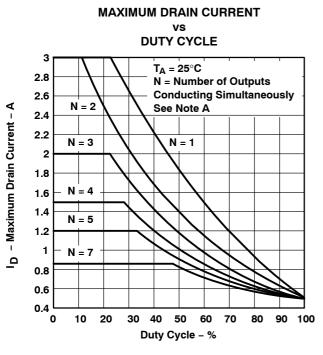


Figure 16. Resistive Switching Waveforms

THERMAL INFORMATION

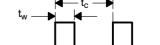


MAXIMUM CLAMP-DIODE CURRENT DUTY CYCLE 3 N = 1 T_A = 25°C 2.8 _{CL} - Maximum Clamp-Diode Current - A N = Number of Outputs 2.6 **Conducting Simultaneously** See Note A 2.4 2.2 2 1.8 N = 21.6 1.4 1.2 N = 31 N = 40.8 N = 50.6 0.4 0.2 70 10 20 30 40 50 60 80 0 90 100 **Duty Cycle - %**

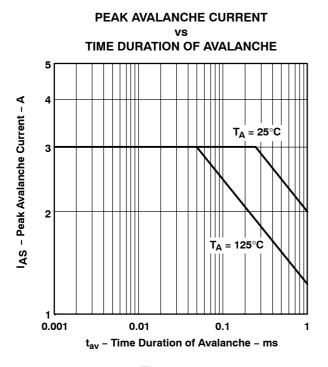
Figure 17

Figure 18

MAXIMUM DRAIN CURRENT



NOTE A: For Figures 17 and 18, $d = t_w/t_c = 10 \text{ ms} / t_c$, where t_w and t_c are defined by the following:



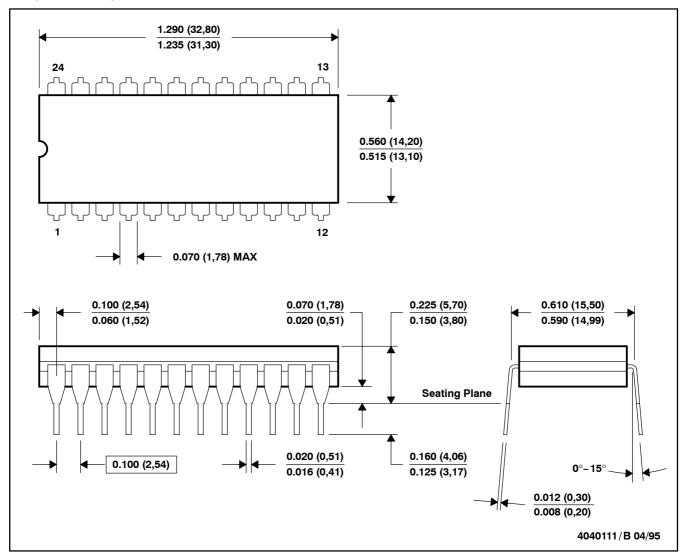
vs **DRAIN-SOURCE VOLTAGE** - Maximum Drain-Diode DCurrent - A 10 6 r_{DS(on)} Limit 4 1 ms 2 **Thermal Limit** 0.6 0.4 0.2 0.1 DC 0.06 0.04 0.02 T_A = 25°C 0.01 0.1 10 100 V_{DS} - Drain-To-Source Voltage - V

Figure 19 Figure 20

MECHANICAL INFORMATION

JW (R-GDIP-T24)

CERAMIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

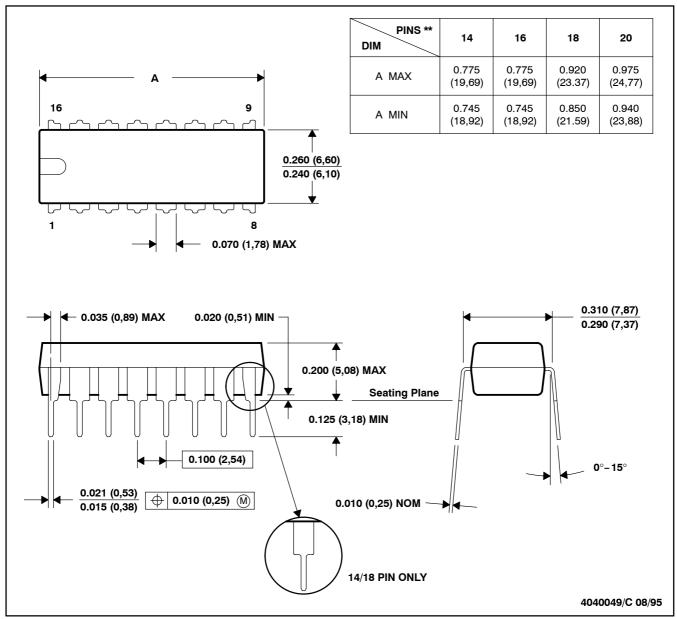
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only
- E. Falls within MIL-STD-1835 GDIP5-T24

MECHANICAL INFORMATION

N (R-PDIP-T**)

16 PIN SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 (20 pin package is shorter then MS-001.)





PACKAGE OPTION ADDENDUM

26-Mar-2007

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPIC2701MJB	OBSOLETE	CDIP	J	24	TBD	Call TI	Call TI
TPIC2701N	OBSOLETE	PDIP	N	16	TBD	Call TI	Call TI

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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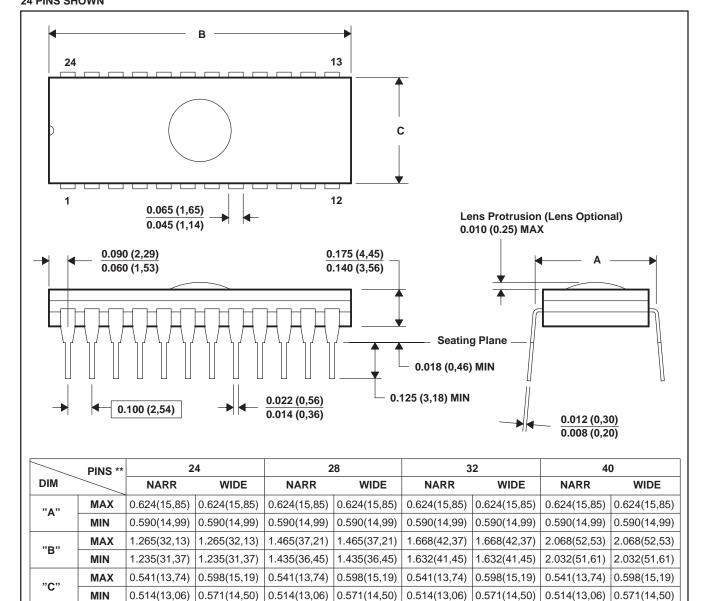
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

4040084/C 10/97

J (R-GDIP-T**)

24 PINS SHOWN

CERAMIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Window (lens) added to this group of packages (24-, 28-, 32-, 40-pin).
- D. This package can be hermetically sealed with a ceramic lid using glass frit.
- E. Index point is provided on cap for terminal identification.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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